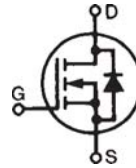


# HiPerFET™ Power MOSFET Q2-Class

## IXFL70N60Q2

(Electrically Isolated Tab)

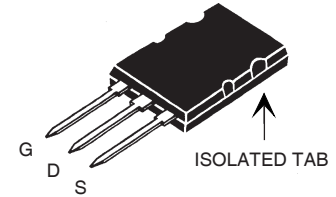


N-Channel Enhancement Mode  
Avalanche Rated, Low  $Q_g$ , Low Intrinsic  $R_G$   
High  $dV/dt$ , Low  $t_{rr}$

$V_{DSS} = 600V$   
 $I_{D25} = 37A$   
 $R_{DS(on)} \leq 92m\Omega$   
 $t_{rr} \leq 250ns$

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	600	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	600	V
$V_{GSS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ C$	37	A
$I_{DM}$	$T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$	280	A
$I_A$	$T_C = 25^\circ C$	35	A
$E_{AS}$	$T_C = 25^\circ C$	5	J
$dV/dt$	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ C$	20	V/ns
$P_D$	$T_C = 25^\circ C$	360	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$	1.6 mm (0.063 in.) from Case for 10s	300	$^\circ C$
$T_{SOLD}$	Plastic body for 10s	260	$^\circ C$
$F_C$	Mounting Force	40..120 / 9..27	N/lb.
$V_{ISOL}$	50/60 Hz, RMS $t = 1$ min $I_{ISOL} \leq 1$ mA $t = 1$ s	2500 3000	V~ V~
<b>Weight</b>		8	g

ISOPLUS264



G = Gate      D = Drain  
S = Source

### Features

- Silicon Chip on Direct-Copper Bond (DCB) Substrate
- Isolated Mounting Surface
- 2500V Electrical Isolation
- Fast Intrinsic Diode
- Avalanche Rated
- Low  $Q_g$
- Low Package Inductance

### Advantages

- High Power Density
- Easy to Mount
- Space Savings

### Applications

- DC-DC Converters
- Battery Chargers
- Switched-Mode and Resonant-Mode Power Supplies
- DC Choppers
- Temperature and Lighting Controls

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 1mA$	600		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 8mA$	3.0		5.5 V
$I_{GSS}$	$V_{GS} = \pm 30V$ , $V_{DS} = 0V$			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$ $T_J = 125^\circ C$			100 $\mu A$ 5 mA
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 35A$ , Note 1			92 m $\Omega$

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 10\text{V}, I_D = 35\text{A}$ , Note 1	36	50	S
$C_{iss}$	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		12	nF
$C_{oss}$			1340	pF
$C_{rss}$			345	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 35\text{A}$ $R_G = 1\Omega$ (External)		26	ns
$t_r$			25	ns
$t_{d(off)}$			60	ns
$t_f$			12	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 35\text{A}$		265	nC
$Q_{gs}$			57	nC
$Q_{gd}$			120	nC
$R_{thJC}$			0.35	$^\circ\text{C/W}$
$R_{thCS}$		0.15		$^\circ\text{C/W}$

### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			70 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			280 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{V}$ , Note 1			1.5 V
$t_{rr}$	$I_F = 25\text{A}, V_{GS} = 0\text{V}$ $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$			250 ns
$Q_{RM}$			1.2	$\mu\text{C}$
$I_{RM}$			8.0	A

Note: 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

**ISOPLUS264™ (IXFL) Outline**

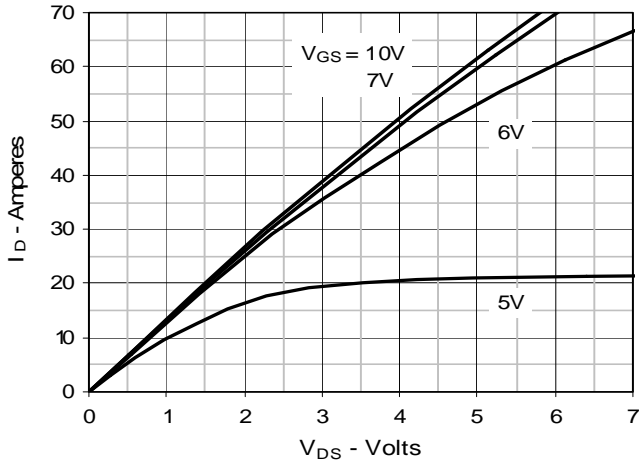
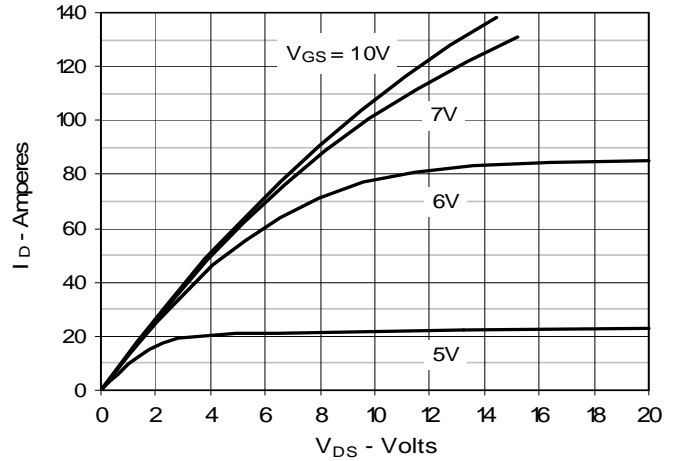
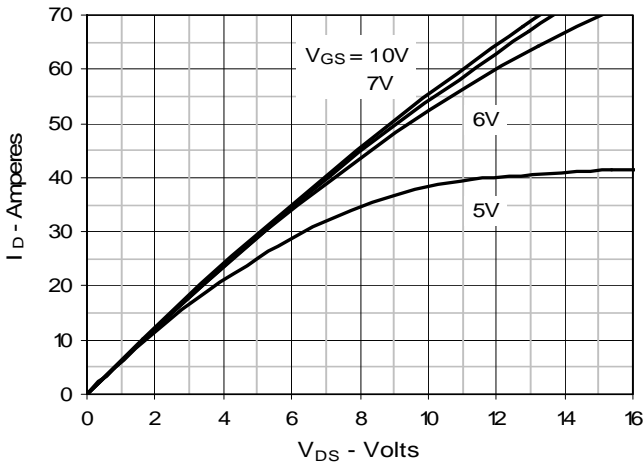
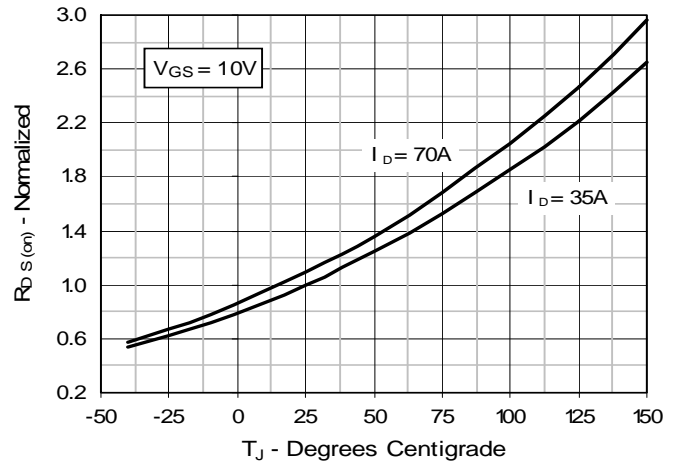
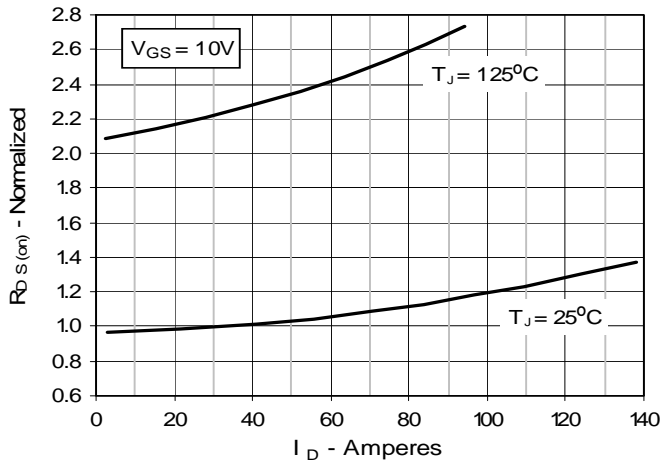
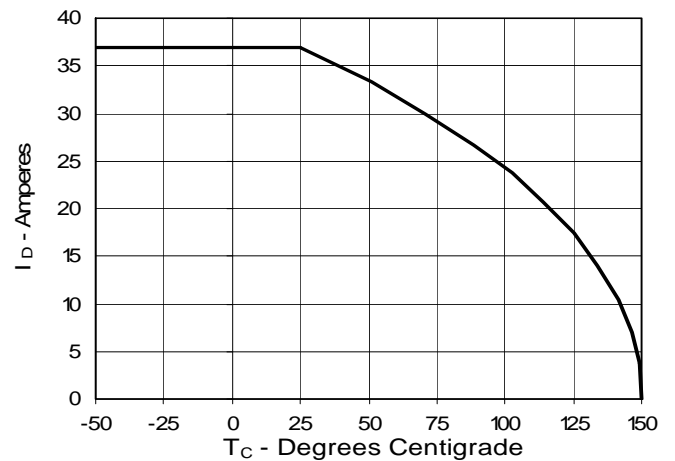
Note: Bottom heatsink meets

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.102	.118	2.59	3.00
A2	.046	.055	1.17	1.40
b	.045	.055	1.14	1.40
b1	.087	.102	2.21	2.59
b2	.111	.126	2.82	3.20
c	.020	.029	0.51	0.74
D	1.020	1.040	25.91	26.42
E	.770	.789	19.56	20.09
e	.215 BSC		5.46 BSC	
L	.780	.820	19.81	20.83
L1	.080	.102	2.03	2.59
Q	.210	.235	5.33	5.97
Q1	.490	.513	12.45	13.03
R	.150	.180	3.81	4.57
R1	.100	.130	2.54	3.30
S	.668	.690	16.97	17.53
T	.801	.821	20.34	20.85
U	.065	.080	1.65	2.03

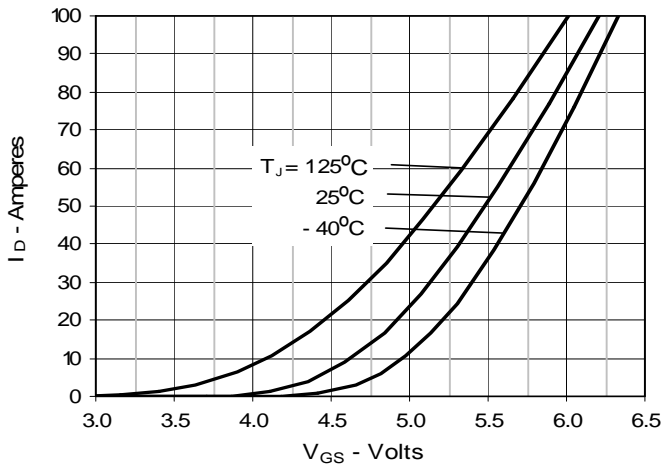
Ref: IXYS CO 0128

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

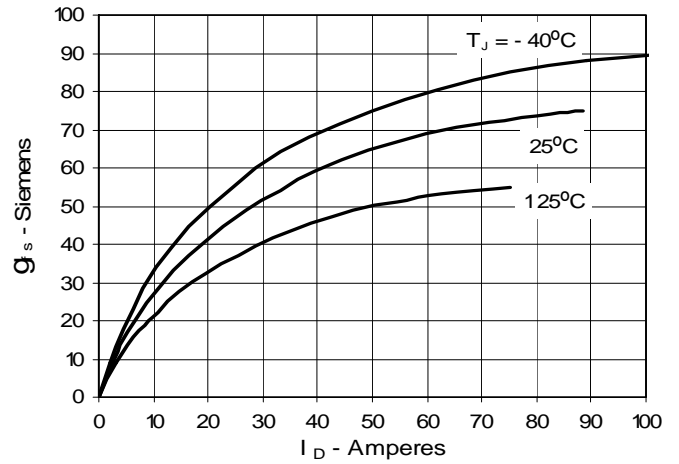
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

**Fig. 1. Output Characteristics**  
 @ 25°C

**Fig. 2. Extended Output Characteristics**  
 @ 25°C

**Fig. 3. Output Characteristics**  
 @ 125°C

**Fig. 4.  $R_{DS(on)}$  Normalized to 0.5  $I_{D25}$  Value vs. Junction Temperature**

**Fig. 5.  $R_{DS(on)}$  Normalized to 0.5  $I_{D25}$  Value vs.  $I_D$** 

**Fig. 6. Drain Current vs. Case Temperature**


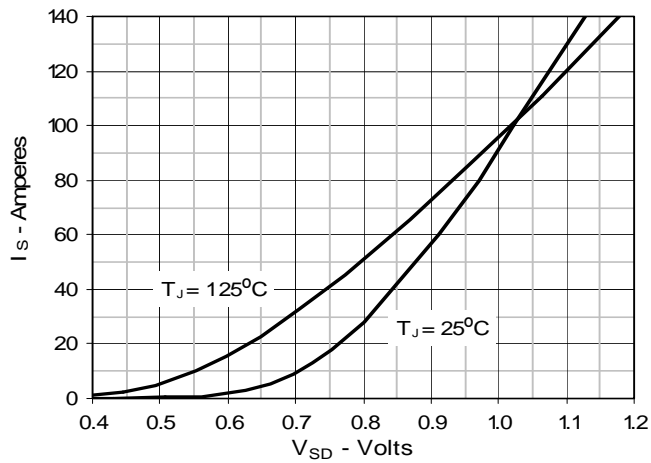
**Fig. 7. Input Admittance**



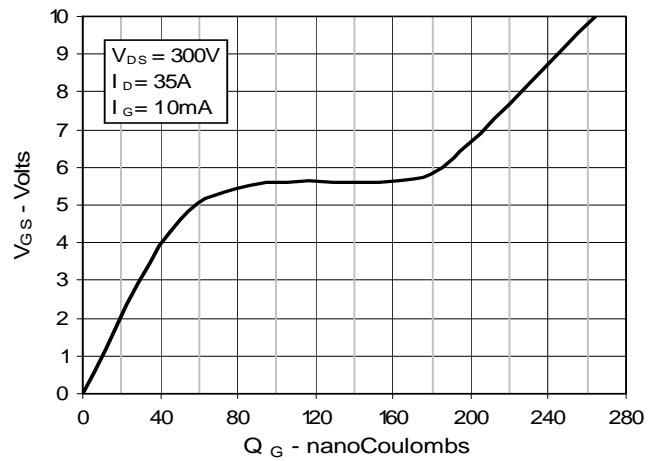
**Fig. 8. Transconductance**



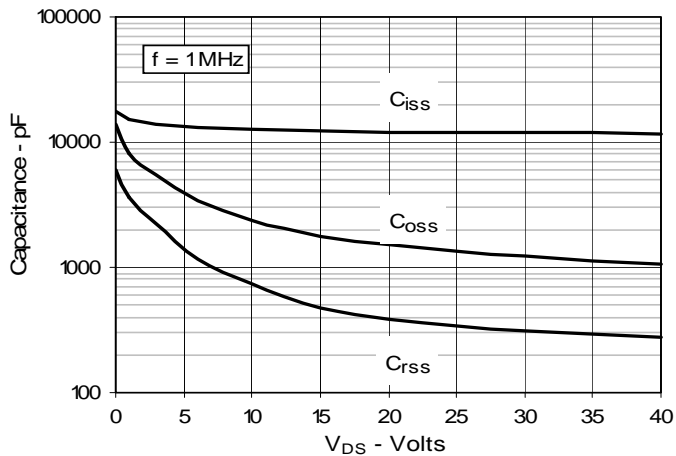
**Fig. 9. Source Current vs. Source-To-Drain Voltage**



**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Maximum Transient Thermal Impedance**

